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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/064,799	08/19/2002	Weng-Hsing Huang	9222-US-PA	4097

31561 7590 05/22/2003

JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE  
7 FLOOR-1, NO. 100  
ROOSEVELT ROAD, SECTION 2  
TAIPEI, 100  
TAIWAN

EXAMINER

CIESLEWICZ, ANETA B

ART UNIT PAPER NUMBER

2814

DATE MAILED: 05/22/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No.

10/064,799

Applicant(s)

HUANG ET AL.

Examiner

Aneta B. Cieslewicz

Art Unit

2814

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☒ Responsive to communication(s) filed on 14 February 2003.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☒ Claim(s) 1-17 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-17 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.  
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

## Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☐ All b) ☐ Some \* c) ☐ None of:  
1. ☐ Certified copies of the priority documents have been received.  
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  
\* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).  
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892) 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 5) ☐ Notice of Informal Patent Application (PTO-152)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_ 6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Claim Rejections - 35 USC § 102*

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

1. Claims 1-5 are rejected under 35 U.S.C. 102(b) as being anticipated by Sogawa et al., US 5,670,402.

**Re claim 1**, Sogawa et al. disclose in Figures 3 and 4 a memory device, comprising substrate (20); gate oxide layer (30), disposed on a surface of the substrate; gate disposed on a portion of the gate oxide layer; buried drain line (36), located in the substrate beside both sides of the gate; spacer (38) disposed on sidewalls of the gate; deep doped region (40) located in the substrate below a part of the buried drain line, wherein the buried drain line and the deep doped region together form a bit line of the memory device; an insulation layer (24), disposed on the gate oxide layer and above the bit line (e.g. column 6, lines 1-2); and a word line (28), disposed above the gate and the insulation layer, perpendicular to a direction of the bit line.

**Re claim 2**, in the memory device disclosed by Sogawa et al. the insulation layer is formed from silicon oxide (e.g. column 6, line 27).

**Re claim 3**, in the memory device disclosed by Sogawa et al. the spacer (38) is formed from silicon oxide (e.g. column 6, line 15).

**Re claim 4**, the memory device disclosed by Sogawa et al. the word line (28) is formed from polysilicon (e.g. column 6, line 55).

**Re claim 5**, in the memory device disclosed by Sogawa et al. the deep-doped region (40) is located in the substrate beside both sides of the spacer.

*Claim Rejections - 35 USC § 103*

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claim 6-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wu, 6,146,949 in view of Sogawa et al., US 5670,402.

**Re claim 6**, Wu discloses a fabrication method for a memory device, comprising:  
forming a gate oxide layer (4) on a substrate (2); forming a bar-shaped conductive structure (6) on the gate oxide layer, wherein a cap layer (8) is formed on a top of the bar-shaped conductive structure; forming a buried drain line (14) in the substrate beside both sides of the bar-shaped conductive structure; forming a spacer (12) on sidewalls of the bar-shaped conductive structure and the cap layer; and forming an insulation layer (16) above the bit line; removing the cap layer (e.g. Figure 7); forming a conductive layer on the substrate and patterning the conductive layer and the bar-shaped conductive structure in a direction perpendicular to a direction of the bit line

to form a word line (18) and a plurality of gates (e.g. column 4, lines 55-59). Wu does not disclose forming a deep doped region in the substrate beside both sides of the spacer, wherein the buried drain line and the deep doped region together form a bit line of the memory device.

Sogawa et al. disclose a fabrication method for a memory device comprising forming a deep-doped region (40) in the substrate below a part of the buried drain line (36). Thus, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the method disclosed by Wu to include the step of forming a deep doped region in the substrate below a part of the buried drain line as disclosed by Sogawa in order to increase reading speed of data (e.g. column 2, lines 15-18).

**Re claim 7**, in the modified method disclosed by Wu, there is an etching selectivity between the cap layer (8) and the spacer (12).

**Re claim 8**, in the modified method disclosed by Wu, there is an etching selectivity between the cap layer (8) and the insulation layer (16).

**Re claim 9**, in the modified method of Wu the cap layer is from silicon nitride (e.g. column 4, line 3).

**Re claim 10**, in the modified method of Wu, the spacer is formed from silicon oxide (e.g. column 4, line 22).

**Re claim 11**, in the modified method of Wu the insulation layer disclosed by Sogawa et al. is formed from silicon oxide (i.e. column 10, line 22).

**Re claim 12**, in the modified method of Wu, forming of the buried drain line (14) includes performing an ion implantation process using the cap layer and the bar-shaped conductive structure as an implantation mask (e.g. Figure 5).

**Re claim 13**, in the modified method of Wu, the deep-doped region (40) disclosed by Sogawa et al. is formed by performing an ion implantation process using the cap layer and the spacer as an implantation mask (e.g. Figure 4c).

**Re claim 14**, in the modified method of Wu forming of the insulation layer above the bit line comprises: forming globally an insulation material on the substrate, the insulation layer covers the cap layer; and removing a portion of the insulation material until the cap layer is exposed (e.g. column 4, lines 34-50).

**Re claim 15**, in the modified method of Wu, removing the portion of the insulation material includes performing back etching or chemical mechanical polishing (e.g. column 4, lines 34-50).

**Re claim 16**, in the modified method of Wu, forming of the bar-shaped conductive structure and the cap layer comprises: forming sequentially a conductive layer and a material (cap) layer on the gate oxide layer; and patterning the material layer and the conductive layer to form the bar-shaped conductive structure and the cap layer (e.g. Figures 2 and 3)

**Re claim 17**, in the modified method of Wu, forming the spacer comprises: forming a conformal silicon layer on the substrate and back-etching the conformal silicon oxide layer to form the spacer (e.g. column 4, lines 22-27).

#### *Response to Arguments*

3. Applicant's arguments with respect to claim 1-17 have been considered but are moot in view of the new ground(s) of rejection.

*Conclusion*

4. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Aneta B. Cieslewicz whose telephone number is (703) 308-7607. The examiner can normally be reached M-F (8:00 a.m. - 4:30 p.m.).


If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached at (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9318 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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ABC  
May 8, 2003



LONG PHAM  
PRIMARY EXAMINER